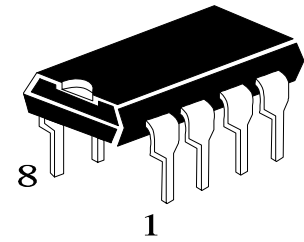


INF85116

2048 x 8 -Bit CMOS EEPROM with I²C-bus interface

The INF85116N is an 16-Kbits (2048 x 8-bit) floating gate Electrically Erasable Programmable Read Only Memory (EEPROM). Power consumption is low due to the full CMOS technology used. The programming voltage is generated on-chip, using a voltage multiplier. As data bytes are received and transmitted via the serial I²C-bus, a package using eight pins is sufficient. Only one INF85116N device is required to support all eight blocks of 256 x 8-bit each.



FEATURES

- Low power CMOS
 - maximum active current 1.0 mA
 - maximum standby current 10 μ A (at 5.5 V), typical 4 μ A
- Non-volatile storage of 16-Kbits organized as eight blocks of 256x8-bits during 20 years (at 55°C)
- Single supply ($U_{cc}=2,7 \div 5,5$ V);
- Automatically increased word's address
- On-chip voltage multiplier
- Serial input/output I²C-bus
- 1000000 ERASE/WRITE cycles per byte
- Internal timer for writing (no external components)
- Write operations: multi byte write mode to 32 bytes
- Write - protection input
- Power-on-reset

Temperature range: -40°C \div +85°C

PIN DESCRIPTION

Symbol	Pin	Description
n. c.	1	not connected
n. c.	2	not connected
n. c.	3	not connected
U _{ss}	4	negative supply voltage
SDA	5	serial data input/output (I ² C-bus)
SCL	6	serial clock input (I ² C-bus)
WP	7	write - protection input
U _{cc}	8	positive supply voltage

PIN CONFIGURATION

n. c.	1	8	U _{cc}
n. c.	2	7	WP
n. c.	3	6	SCL
U _{ss}	4	5	SDA

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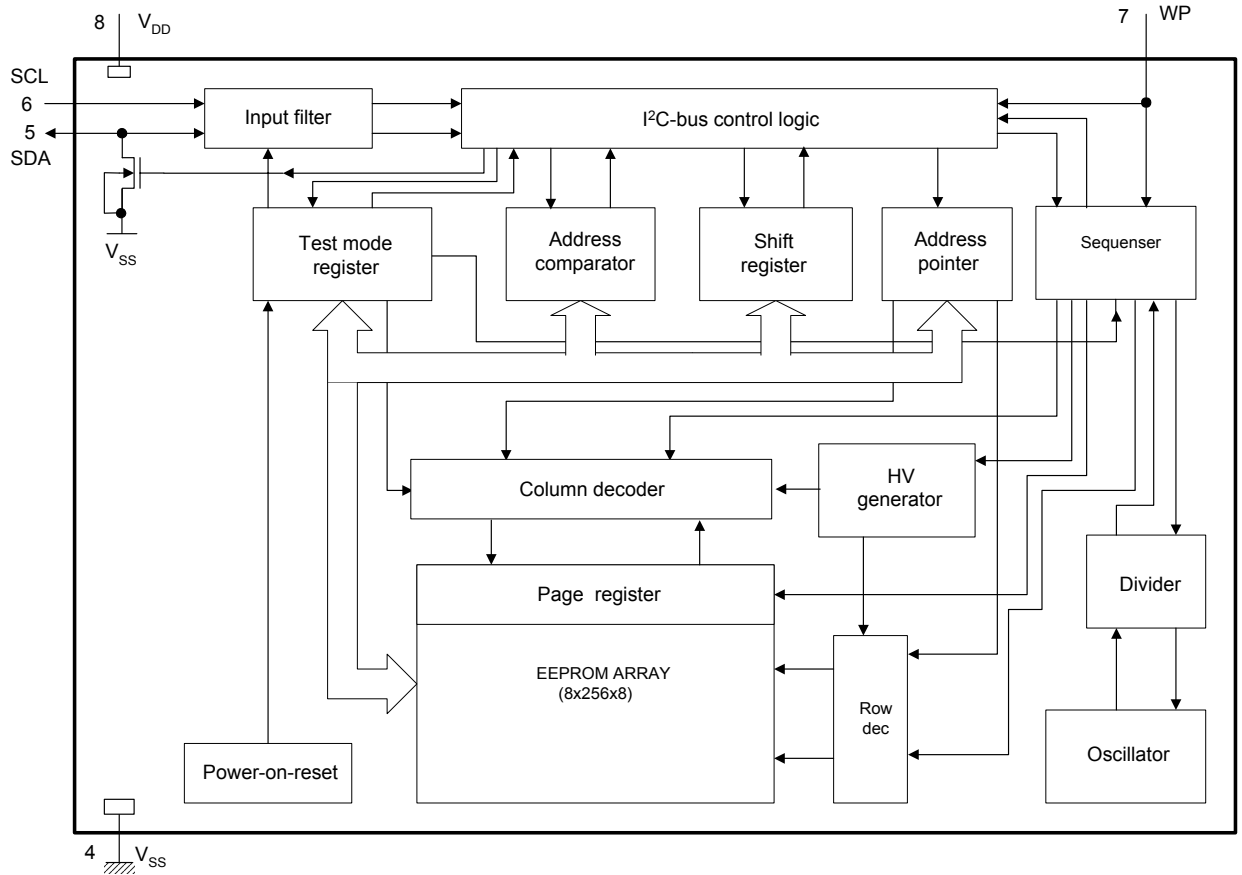
Table 1. Quick reference data

Symbol	Parameter	min	max	Unit
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U_{DD}	Supply voltage	2.7	5.5	V
I_{OL}	LOW level output current	-	6	mA
T_{amb}	Operating ambient temperature	-40	+85	°C

BLOCK DIAGRAM**Table 2. Limiting values**

Symbol	Parameter	min	max	Unit
U_{DD}	Supply voltage	-0.3	6.5	V
U_i	Input voltage on any pin $ Z_i > 500 \Omega$	-0.8	6.5	V
i_i	Input current on any pin	-	1	mA
i_o	Output current	-	10	mA
T_{stg}	Storage temperature	-65	+150	°C



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Table 3. Characteristics

Symbol	Parameter	Conditions	min	max	Unit
$I_{DD(stb)}$	Standby supply current	$U_{DD} = 2.7V$	-	6	μA
		$U_{DD} = 5.5V$		10	μA
I_{CCR}	Supply current READ	$f_{SCL}=400kHz,$ $U_{DD} = 5.5V$	-	1	mA
I_{CCW}	Supply current E / W	$f_{SCL}=400kHz,$ $U_{DD} = 5.5V$	-	1	mA
WP input (pin 7)					
U_{IL}	LOW level input voltage		-0.8	$+0.1U_{DD}$	V
U_{IH}	HIGH level input voltage		$0.9U_{DD}$	$U_{DD}+0.8$	V
SCL input (pin 6)					
U_{IL}	LOW level input voltage		-0.8	$+0.3U_{DD}$	V
U_{IH}	HIGH level input voltage		$0.7U_{DD}$	6.5	V
I_{LI}	Input leakage current	$U_I=U_{DD}$ or U_{SS}	-	± 1	μA
f_{SCL}	Clock input frequency		0	400	kHz
t_{sp}	Pulse width of spikes suppressed by filter		0	100	ns
C_1	Input capacitance	$U_I= U_{SS}$	-	7	pF
SDA input/output (pin 5)					
U_{IL}	LOW level input voltage		-0.8	$0.3U_{DD}$	V
U_{IH}	HIGH level input voltage		$0.7U_{DD}$	6.5	V
U_{OL1} U_{OL2}	LOW level output voltage	$I_{OL}=3mA,$ $U_{DD} = U_{DD (min)}$ $I_{OL}=6mA,$ $U_{DD} = U_{DD (min)}$	-	0.4 0.6	V
I_{LO}	Output leakage current	$U_{OH}=U_{DD}$	-	1	μA
$t_{O(F)}$	Output fall time from U_{IHmin} to U_{ILmax}	with up to 3mA sink current at U_{OL1}	$20+0.1 C_B^*$	250	ns
		with up to 6mA sink current at U_{OL2}	$20+0.1 C_B$	250	ns
t_{SP}	Pulse width of spikes suppressed by filter		0	100	ns
C_1	Input capacitance	$U_I=0V$	-	10	pF
$t_{E/W}$	E/W cycle time		-	10	ms
$N_{E/W}$	E/W cycle per byte	$T_{amb} = (-40+85) ^\circ C,$	100000	-	
		$T_{amb} = 22^\circ C$	1000000		
t_S	Data retention time	$T_{amb} = 55^\circ C$	20	-	years

* - The bus capacitance ranges from 10 to 400pF (C_B = total capacitance of one bus line in pF)



INF85116**Table 4. I²C-bus characteristics**

Symbol	Parameter	Condi- tions	Standard mode		Fast mode		Unit
			min	max	min	max	
f _{SCL}	Clock frequency		0	100	0	400	kHz
t _{BUF}	Time the bus must be free before	-	4.7	-	1.3	-	μs
t _{HD, STA}	START condition hold time after which first clock pulse is generated	-	4.0	-	0.6	-	μs
t _{LOW}	LOW level clock period	-	4.7	-	1.3	-	μs
t _{HIGH}	HIGH level clock period	-	4.0	-	0.6	-	μs
t _{SU, STA}	Set-up time for START condition	repeated start	4.7	-	0.6	-	μs
t _{HD, DAT}	Data hold time for CBUS compatible masters	-	5	-	-	-	μs
t _{HD, DAT}	Data hold time for I ² C - bus devices	note 1	0	-	0	-	ns
t _{SU, DAT}	Data set-up time	-	250	-	100	-	ns
t _R	SDA and SCL rise time	-	-	1000	20+0.1 C _b ⁽²⁾	300	ns
t _F	SDA and SCL fall time	-	-	300	20+0.1 C _b ⁽²⁾	300	ns
t _{SU, STO}	Set-up time for STOP condition	-	4.0	-	0.6	-	μs

Notes:

1. The hold time required (not greater than 300 ns) to bridge the undefined region of the falling edge of SCL must be internally provided by a transmitter.
2. C_b = total capacitance of one bus line in pF.

